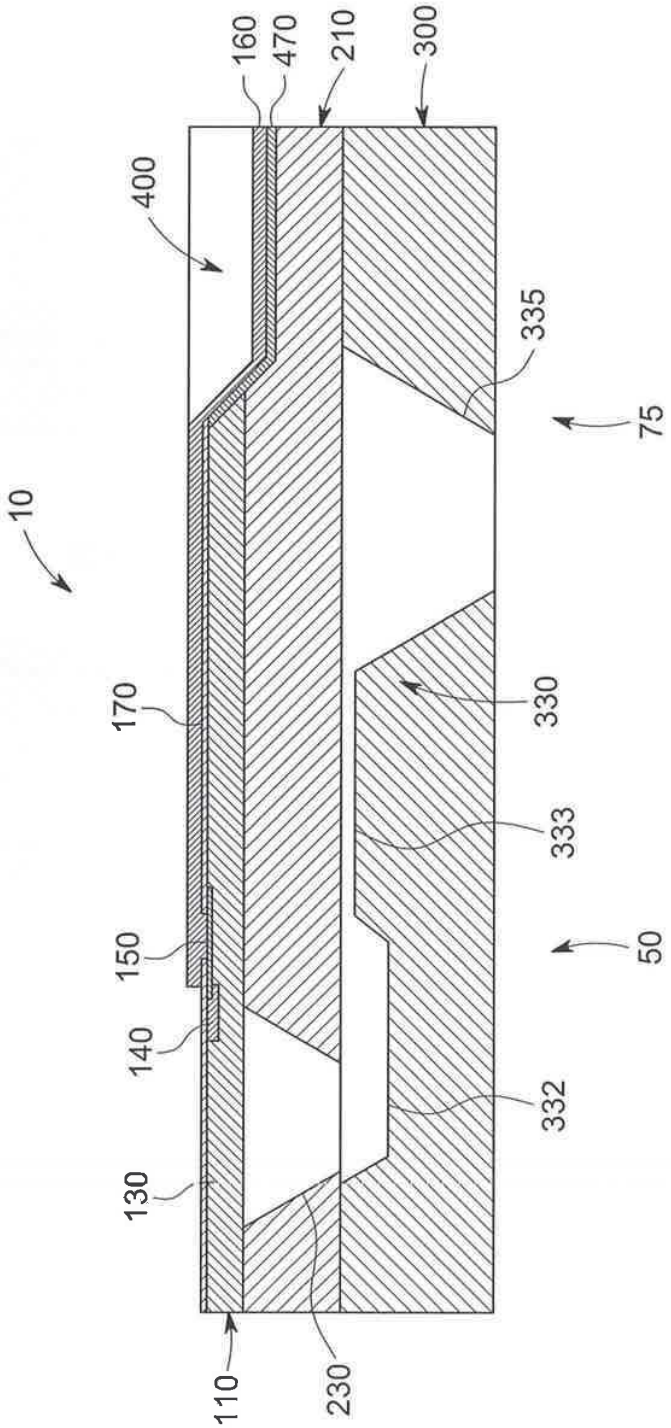

160
470
210
300
400
335
75
10
170
330
333
150
50
140
332
130
110
230

FIG. 1

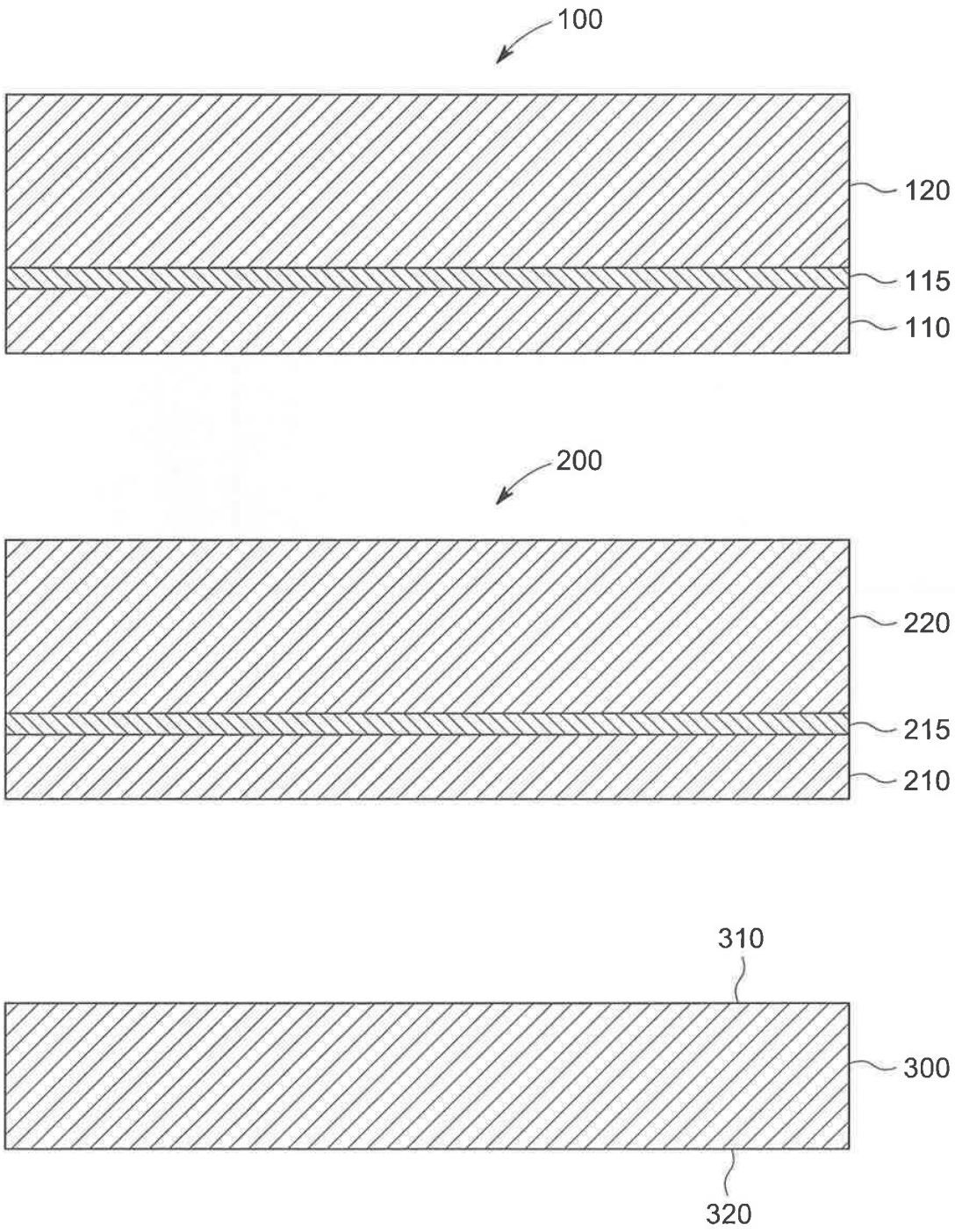


FIG. 2

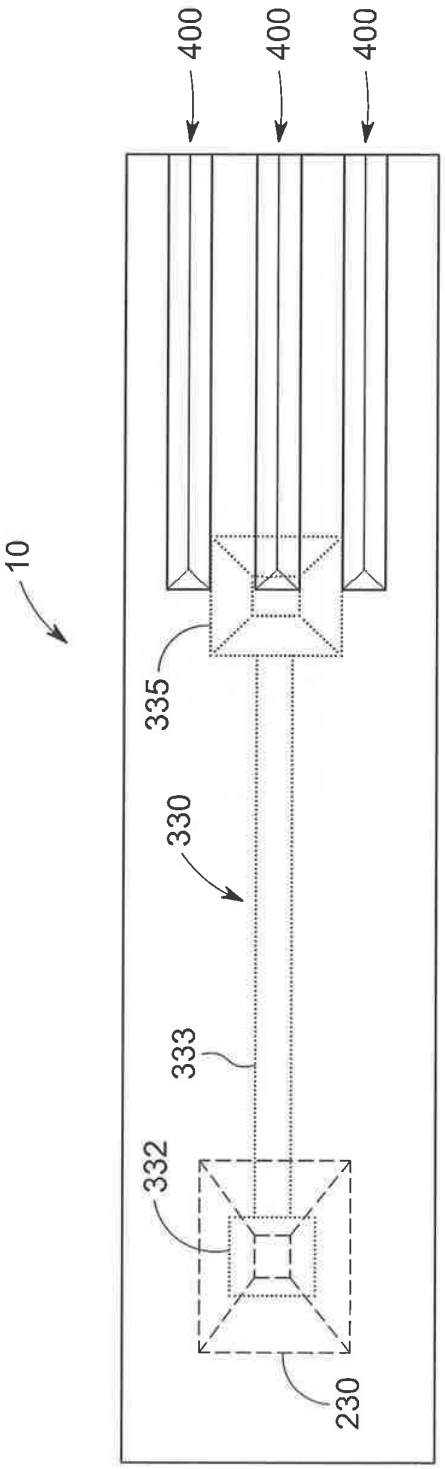

10
400
400
400
335
330
333
332
230

FIG. 3

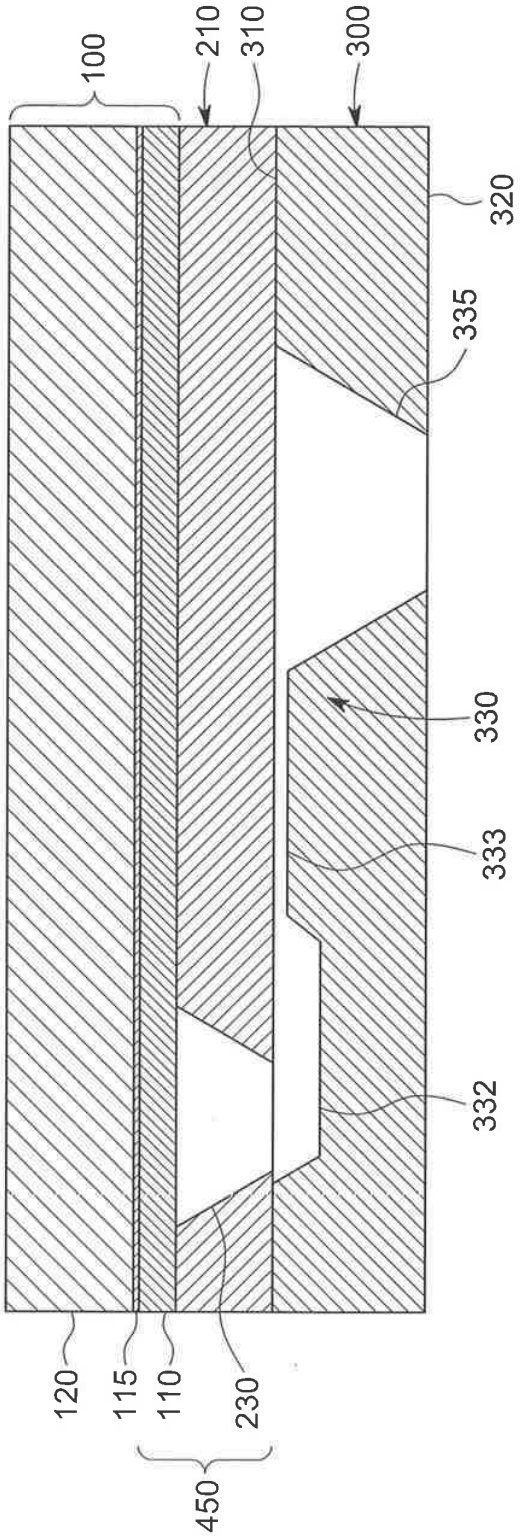

100
210
310
300
320
335
330
333
332
120
115
110
230
450

FIG. 4

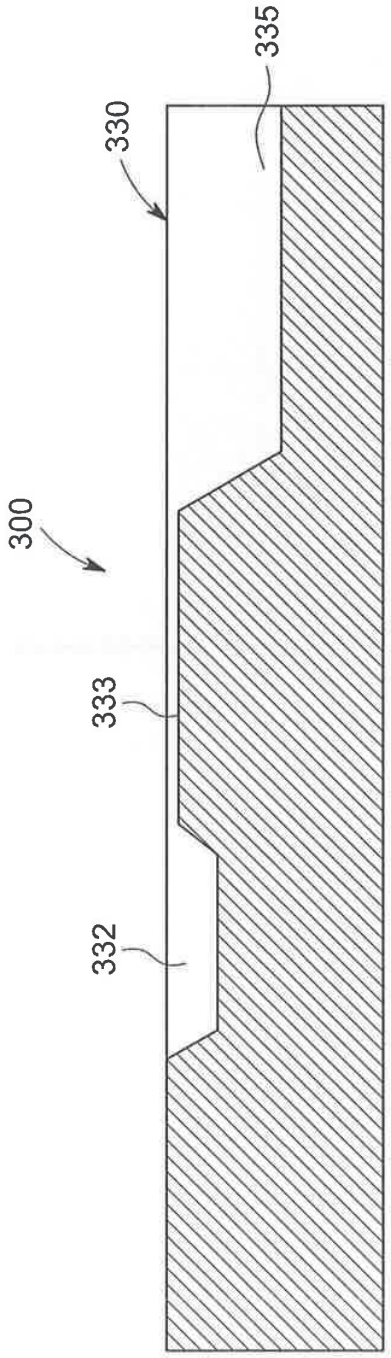


FIG. 5

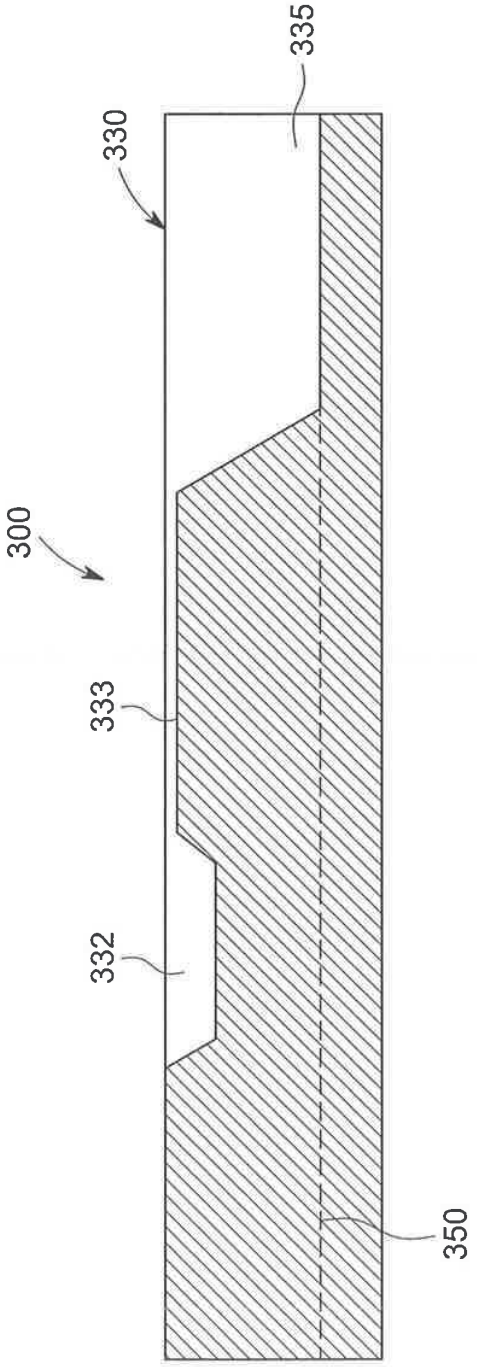


FIG. 6

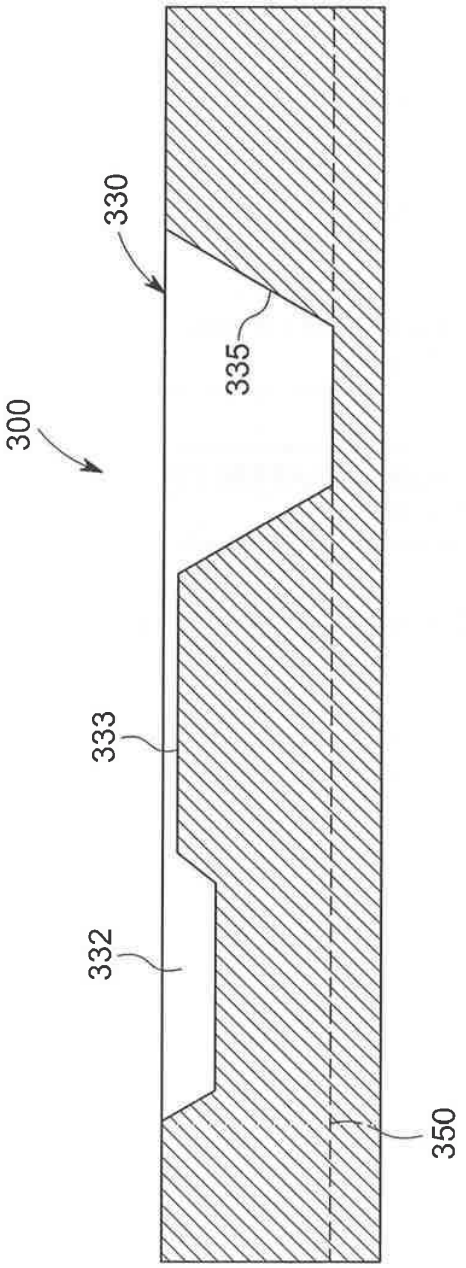

300
330
335
333
332
350

FIG. 7

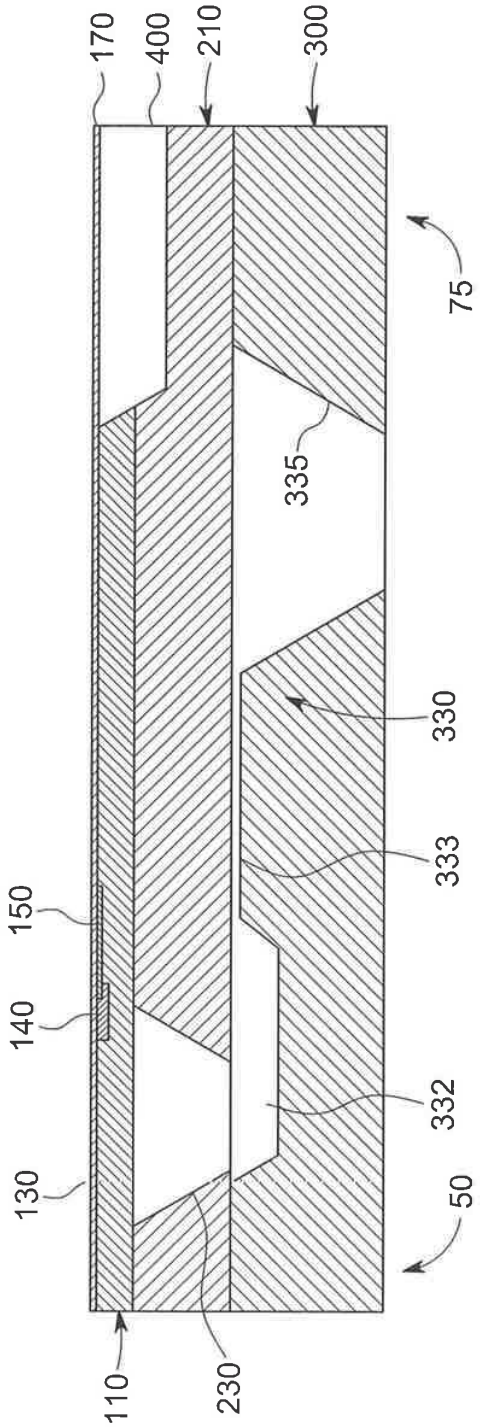

170
400
210
300
75
335
330
333
150
140
332
130
50
110
230

FIG. 8

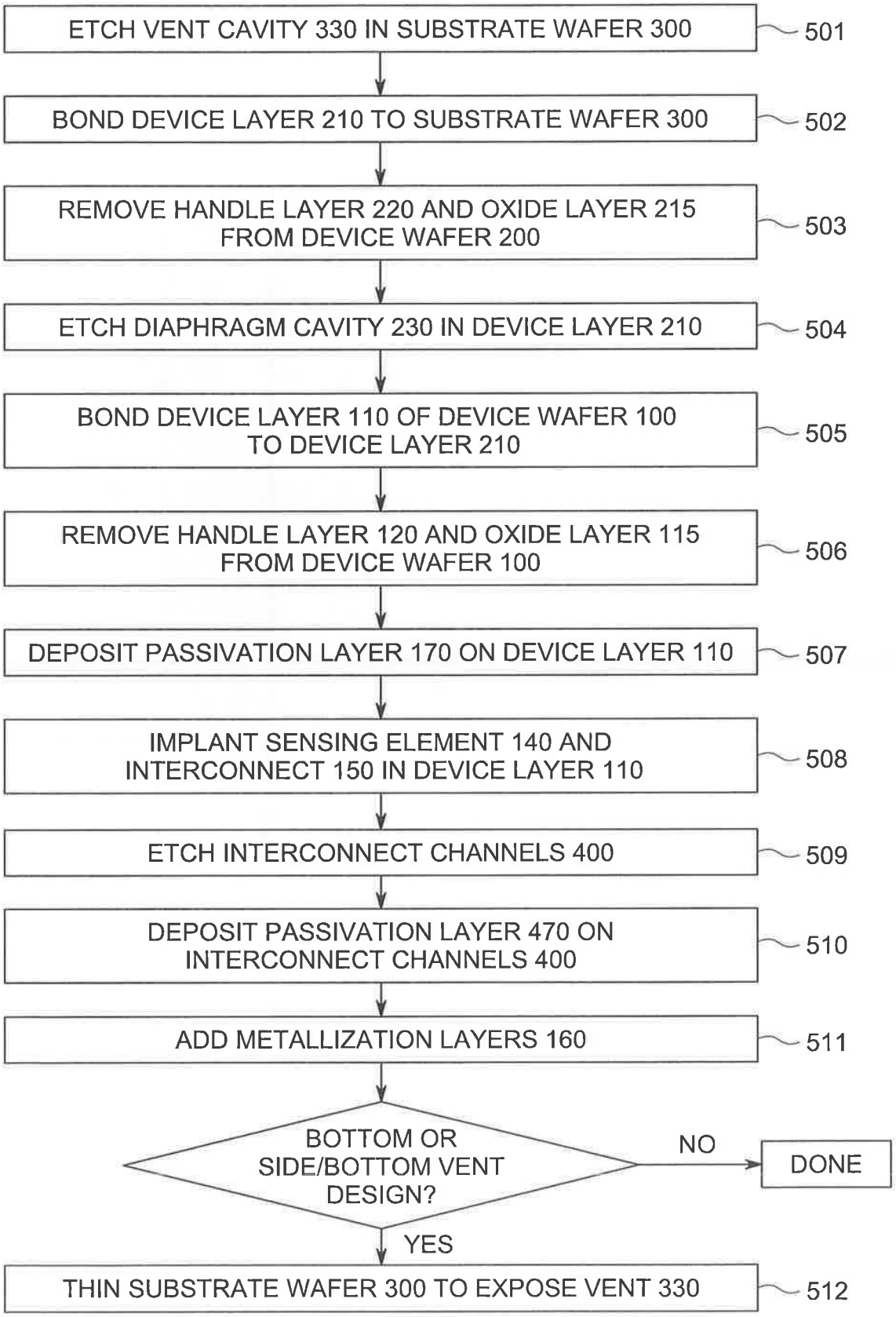

ETCH VENT CAVITY 330 IN SUBSTRATE WAFER 300
501
BOND DEVICE LAYER 210 TO SUBSTRATE WAFER 300
502
REMOVE HANDLE LAYER 220 AND OXIDE LAYER 215 FROM DEVICE WAFER 200
503
ETCH DIAPHRAGM CAVITY 230 IN DEVICE LAYER 210
504
BOND DEVICE LAYER 110 OF DEVICE WAFER 100 TO DEVICE LAYER 210
505
REMOVE HANDLE LAYER 120 AND OXIDE LAYER 115 FROM DEVICE WAFER 100
506
DEPOSIT PASSIVATION LAYER 170 ON DEVICE LAYER 110
507
IMPLANT SENSING ELEMENT 140 AND INTERCONNECT 150 IN DEVICE LAYER 110
508
ETCH INTERCONNECT CHANNELS 400
509
DEPOSIT PASSIVATION LAYER 470 ON INTERCONNECT CHANNELS 400
510
ADD METALLIZATION LAYERS 160
511
BOTTOM OR SIDE/BOTTOM VENT DESIGN?
NO
DONE
YES
THIN SUBSTRATE WAFER 300 TO EXPOSE VENT 330
512

FIG. 9

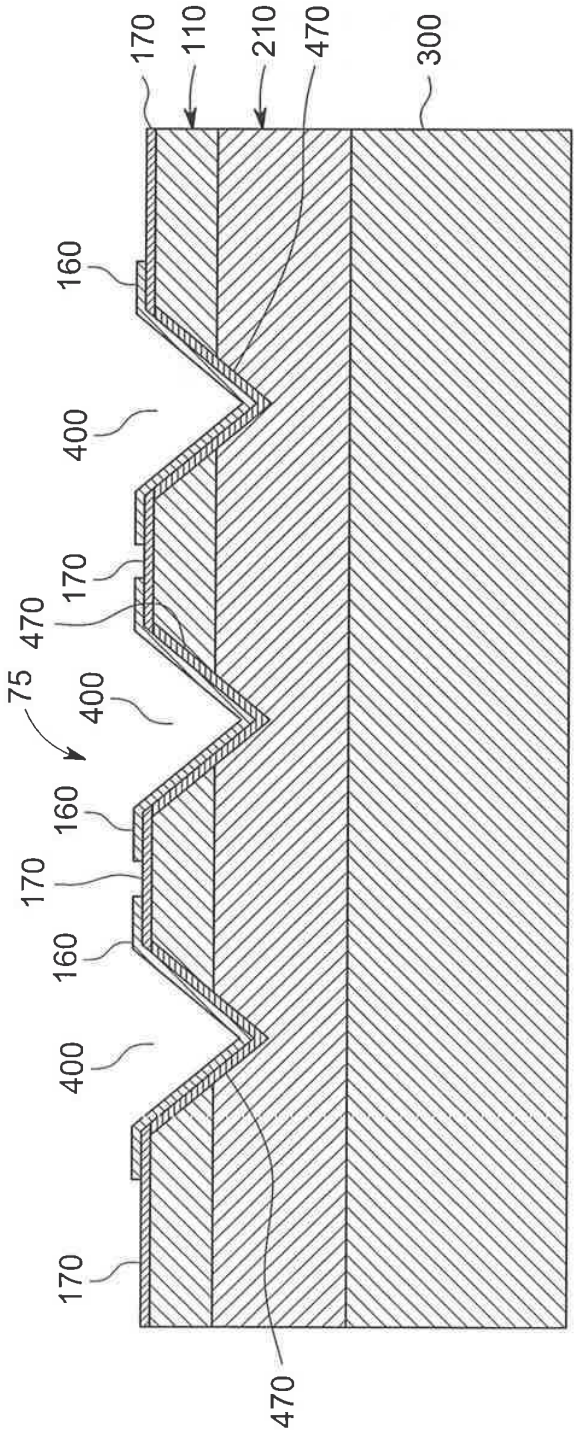

170
110
210
470
300
160
400
170
470
75
400
160
170
160
400
170
470

FIG. 10

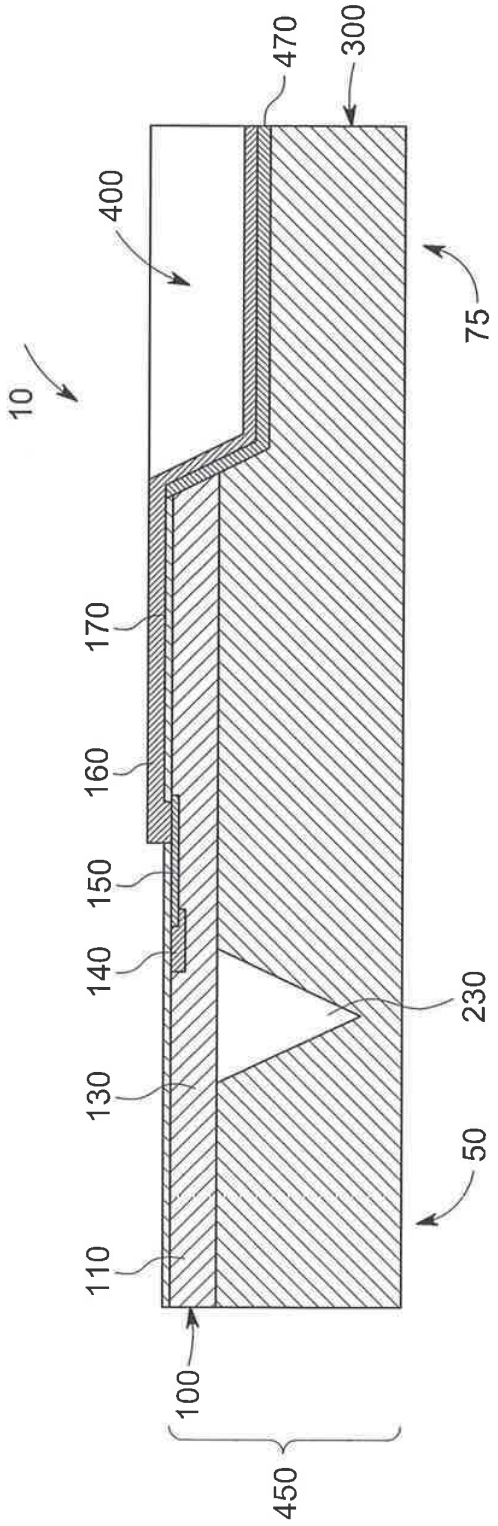

470
300
400
75
10
170
160
150
140
230
130
50
110
100
450

FIG. 11

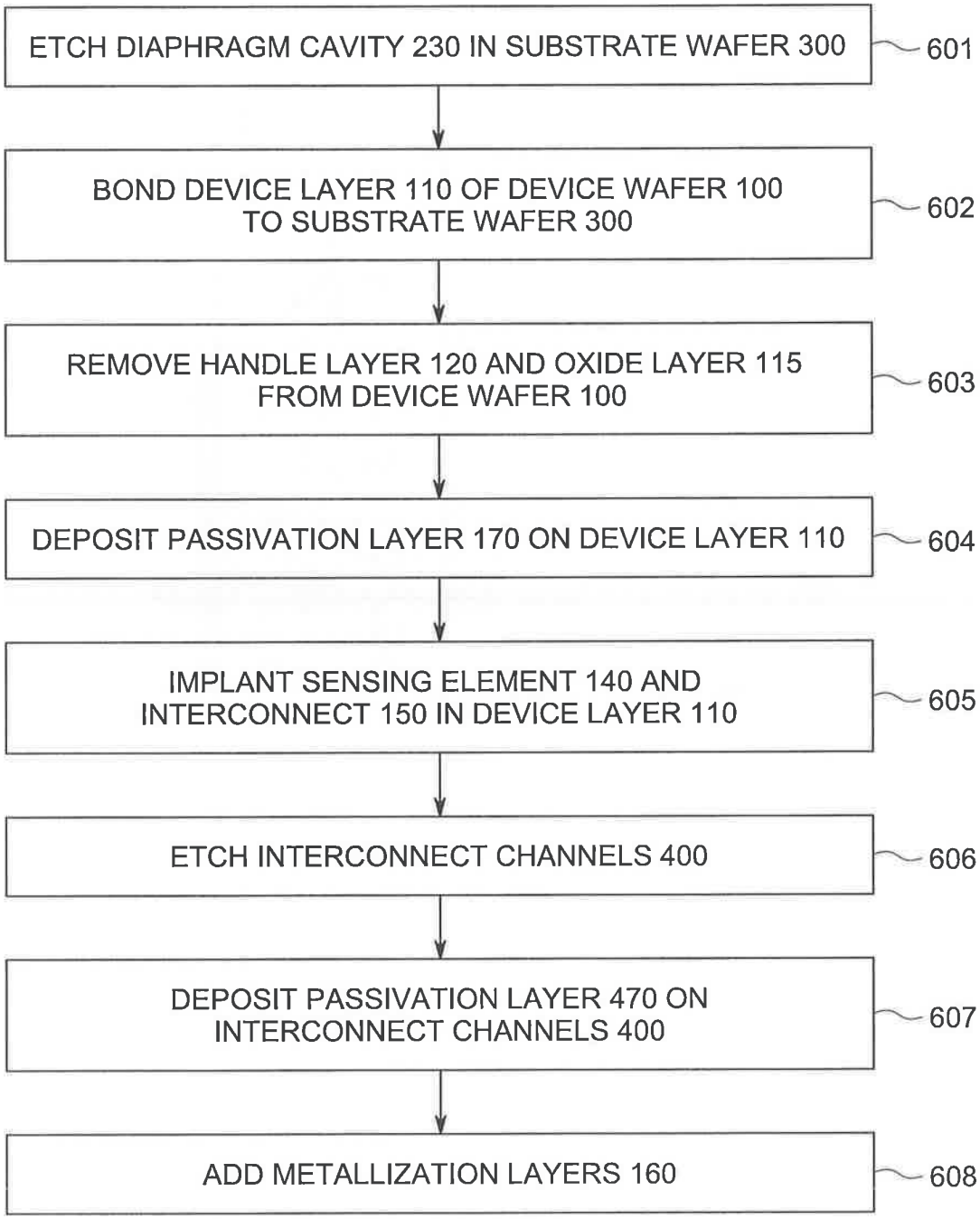

ETCH DIAPHRAGM CAVITY 230 IN SUBSTRATE WAFER 300
601
BOND DEVICE LAYER 110 OF DEVICE WAFER 100 TO SUBSTRATE WAFER 300
602
REMOVE HANDLE LAYER 120 AND OXIDE LAYER 115 FROM DEVICE WAFER 100
603
DEPOSIT PASSIVATION LAYER 170 ON DEVICE LAYER 110
604
IMPLANT SENSING ELEMENT 140 AND INTERCONNECT 150 IN DEVICE LAYER 110
605
ETCH INTERCONNECT CHANNELS 400
606
DEPOSIT PASSIVATION LAYER 470 ON INTERCONNECT CHANNELS 400
607
ADD METALLIZATION LAYERS 160
608

FIG. 12

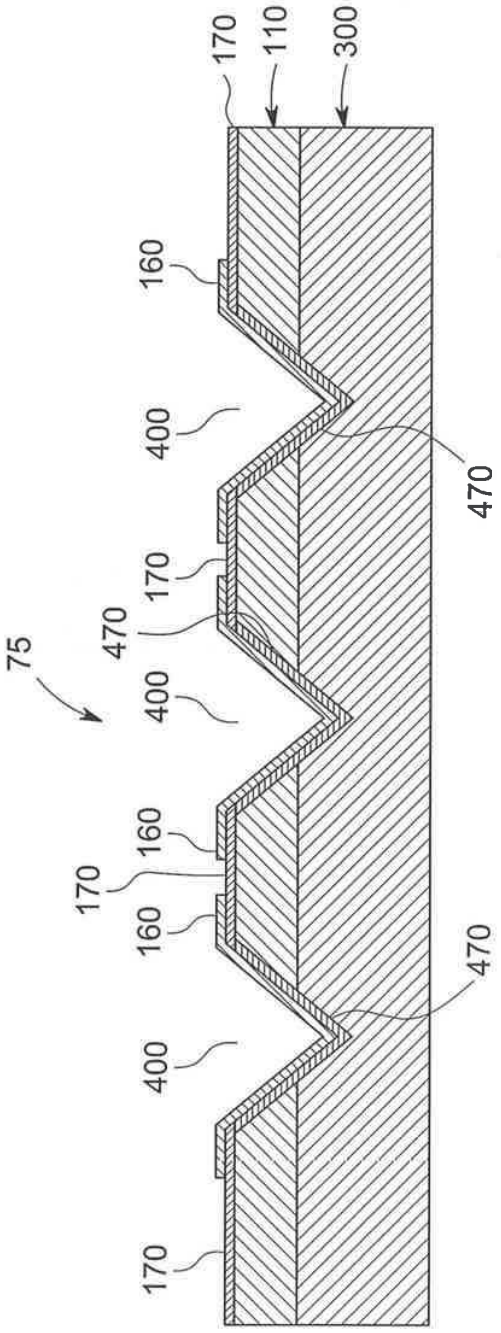


FIG. 13